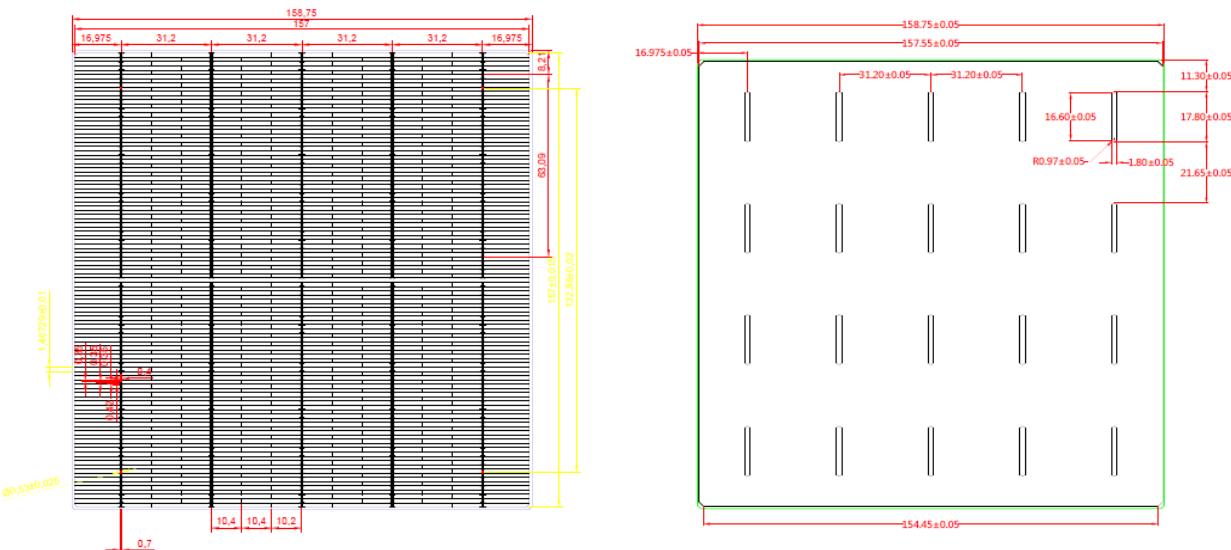


• 技术图形 Technical drawing



• 电气特性 Electrical Characteristics

Grade	Eff(%)	Pmpp(W)	Vmpp(V)	Impp(A)	Voc(V)	Isc(A)	FF(%)
1	22.60	5.70	0.589	9.668	0.682	10.1723	82.16
2	22.50	5.67	0.588	9.643	0.681	10.1592	81.94
3	22.40	5.64	0.587	9.617	0.680	10.1409	81.88
4	22.30	5.62	0.586	9.599	0.679	10.1331	81.67
5	22.20	5.59	0.584	9.578	0.678	10.1158	81.53
6	22.10	5.57	0.582	9.564	0.677	10.0943	81.49
7	22.00	5.54	0.581	9.548	0.676	10.0830	81.29
8	21.90	5.52	0.579	9.525	0.675	10.0785	81.08

标准测试条件下(Under standard test condition) :1000W/m², AM1.5, 25°C

温度系数 Temperature coefficients

开路电压温度系数 Temperature coefficients of open circuit voltage: -0.37%/K

短路电流温度系数 Temperature coefficients of short circuit current: +0.07%/K

最大功率温度系数 Temperature coefficients of maximum power: -0.36%/K

• 机械特征 Mechanical characteristics

尺寸规格 Dimension:	158.75mmx158.75mm±0.25mm, Φ223mm±0.25mm; 电池厚度 Cell Thickness:	170+20/-10μm
正面（-） Front side: 二氧化硅+深蓝色氮化硅复合减反膜 (PID Free); 主栅宽度: 0.7±0.1mm; 108 根副栅线, 正电极为半片双防断栅设计。		
Silicon oxide+blue silicon nitride compound anti-reflection coating(PID Free);The width of the busbar is 0.7±0.1mm;the number of the finger is 108;The front side of solar cell is designed as a half double-guard gate sheet.		
背面（+） Back side: 钝化发射极 (氧化铝及氮化硅复合层); 背电极四段式宽度为 1.6±0.3mm。		
Passivated Emitter (AlOx and SiNx dual layer) rear contact;The width and length of the Ag electrode is 1.6±0.3mm.		
可焊性 (Solderability): 最小剥离强度 (Peel strength) ≥1.45N/mm, 结果可能会因焊条、焊接方法及条件而不同。Results may vary depending on the conditions.		